



RESPONSE UNDER 37 CFR 1.116  
EXPEDITED PROCEDURE  
EXAMINING GROUP 2818

PATENT APPLICATION

Do. No. 5484-093

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Byeong-Hoon LEE, et al.

Serial No. 09/997,080

Examiner: Phan, Trong Q

Confirmation No. 6095

Filed: November 28, 2001

Group Art Unit: 2818

For: NONVOLATILE SEMICONDUCTOR MEMORY DEVICE

BOX AF

Assistant Commissioner for Patents  
Washington, D.C. 20231

Do not enter  
TP  
1/24/03

TECHNOLOGY CENTER 2800

RECEIVED  
JAN 17 2003

M. Brauns on  
2/26/03

AMENDMENT AFTER FINAL REJECTION UNDER 37 CFR 1.116

Responsive to the Final Office Action, dated November 14, 2002, please amend the application as follows.

IN THE CLAIMS

A full set of pending claims is reproduced below for the Examiner's convenience.

1. A nonvolatile semiconductor memory device comprising:  
a plurality of sectors;  
each sector comprising memory cell transistors arranged in a cell array block and decoder transistors in a column decoder block;  
wherein the transistors in the cell array block and column decoder block in each sector share a common bulk region; and  
wherein said semiconductor memory device is configured to electrically erase all the memory cell transistors in a sector together.
2. A nonvolatile semiconductor memory device according to claim 1, wherein the semiconductor memory device is a NOR-type memory device.

01/17/2003 BABRAHA1 00000064 09997080

01 FC:1202  
02 FC:1201

90.00 OP  
420.00 OP